

Ordering number : ENN7017

P-Channel Silicon MOSFET



**CPH6313**

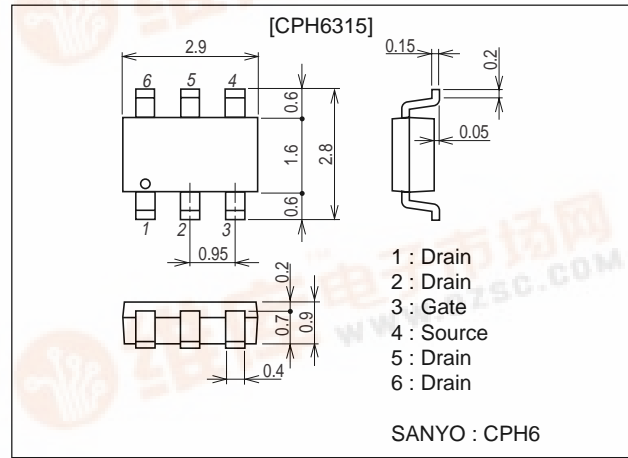
**High-Speed Switching Applications**

**Features**

- Low ON-resistance.
- High-speed switching.
- 2.5V drive.

**Package Dimensions**

unit : mm  
2151A



**Specifications**

**Absolute Maximum Ratings** at Ta=25 °C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-20	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		-4	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-16	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (1200mm²X0.8mm)	1.6	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25 °C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR) <sub>DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0	-20			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0			-1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A	4	5.8		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-2A, V <sub>GS</sub> =-4.5V		55	72	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-1A, V <sub>GS</sub> =-2.5V		80	110	mΩ

Marking : JP

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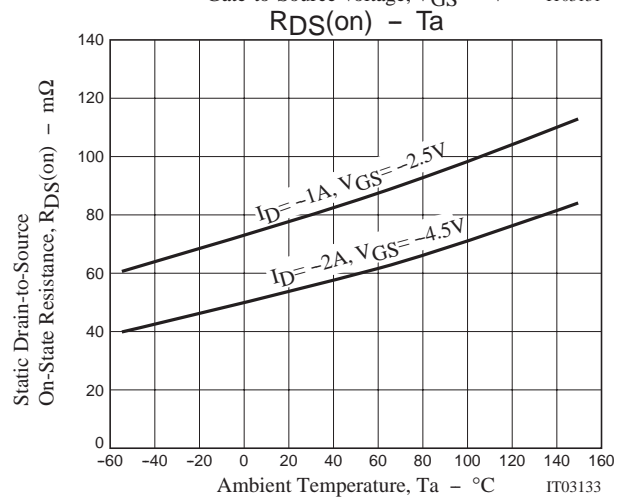
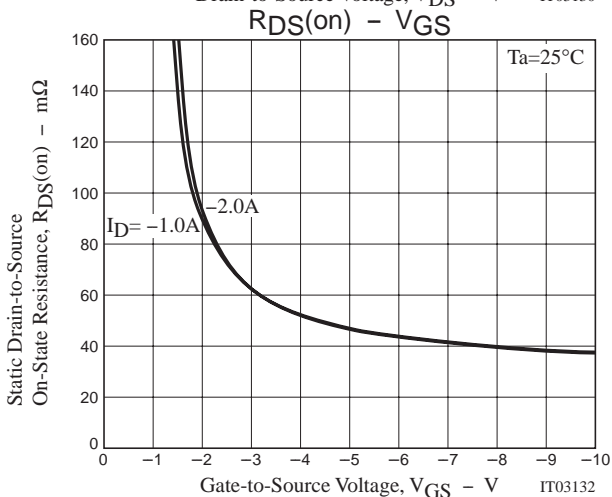
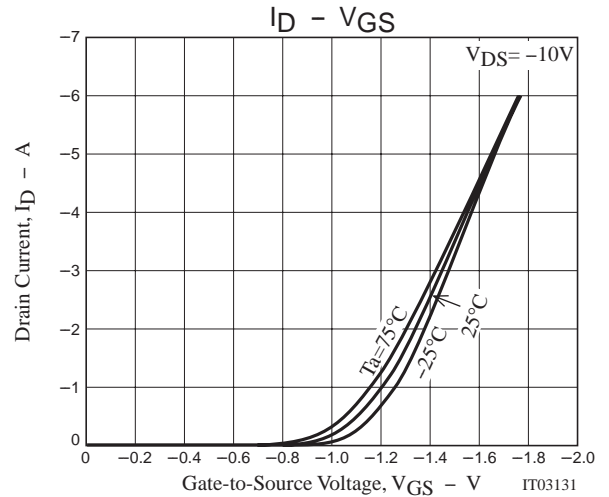
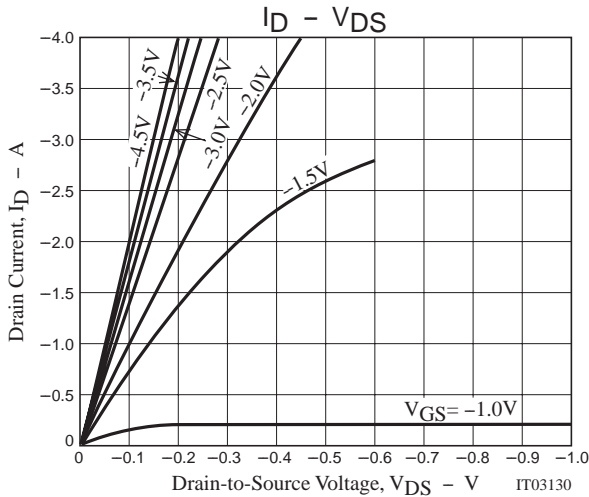
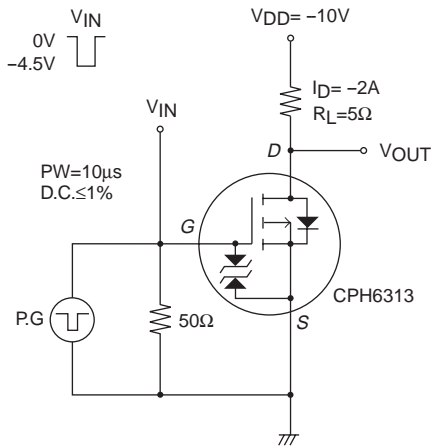


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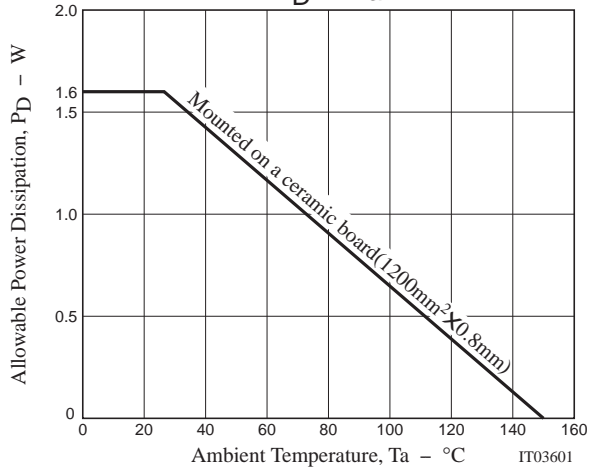
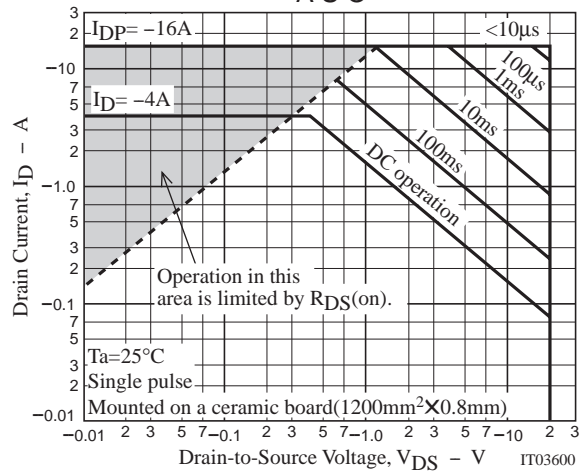
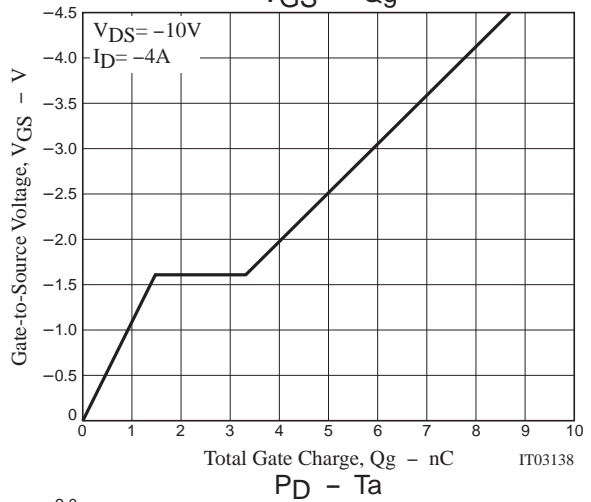
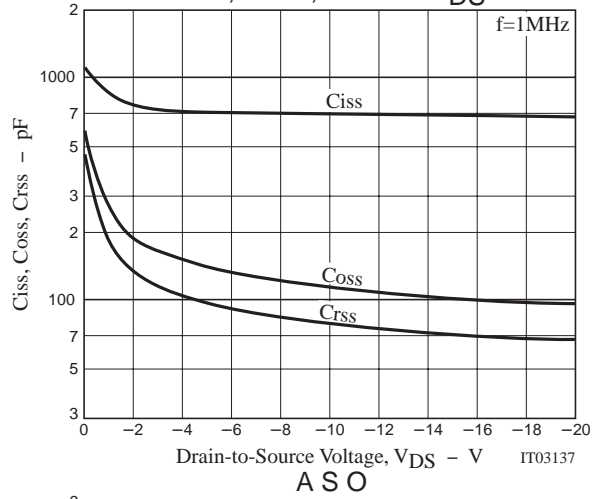
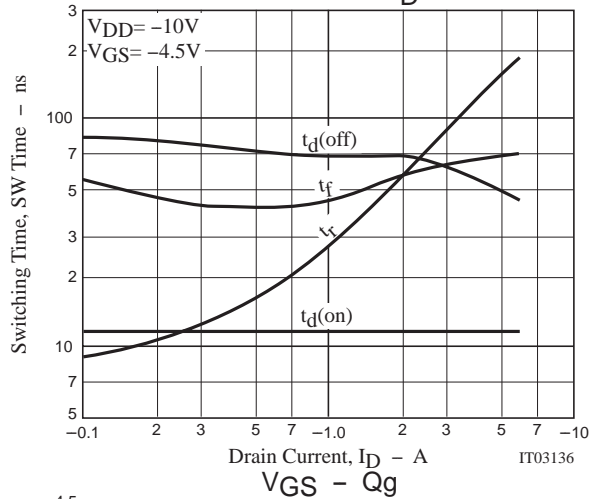
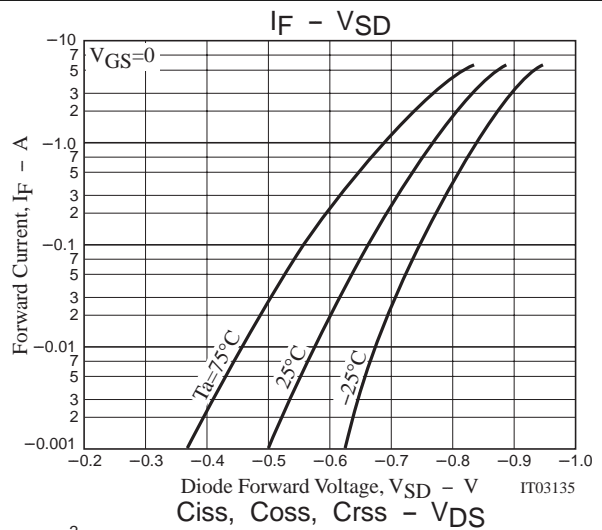
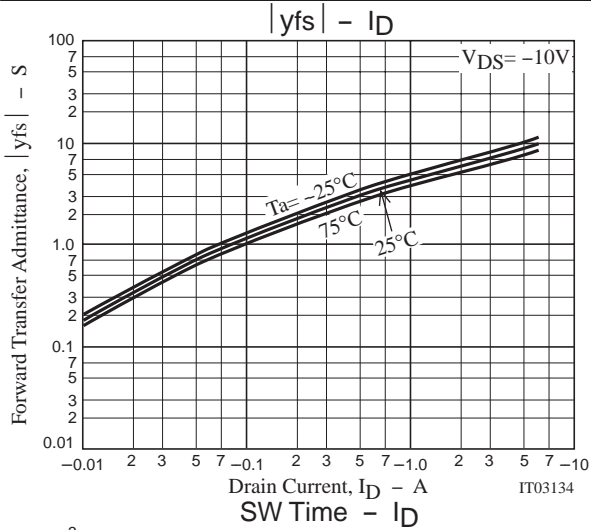
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	$V_{DS}=-10V, f=1MHz$		680		pF
Output Capacitance	Coss	$V_{DS}=-10V, f=1MHz$		115		pF
Reverse Transfer Capacitance	Crss	$V_{DS}=-10V, f=1MHz$		80		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		12		ns
Rise Time	$t_r$	See specified Test Circuit.		57		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		68		ns
Fall Time	$t_f$	See specified Test Circuit.		58		ns
Total Gate Charge	Qg	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-4A$		8.7		nC
Gate-to-Source Charge	Qgs	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-4A$		1.5		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-4A$		1.8		nC
Diode Forward Voltage	$V_{SD}$	$I_S=-4A, V_{GS}=0$		-0.85	-1.2	V

## Switching Time Test Circuit



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